



SHEET 1 OF 1

FORM PTO - 1449

SUPPLEMENTAL INFORMATION
DISCLOSURE STATEMENT

ATTORNEY DOCKET NO.: ASC-058A

APPLICANTS: Leitz *et al.*

SERIAL NO.: 10/647,074

FILING DATE: August 22, 2003

GROUP: 2812

U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>Lee</i>	B52	02/13262	02/14/2002	WO				N	Y
<i>Lee</i>	B53	03/105189	12/18/2003	WO				N	Y
<i>Lee</i>	B54	0 353 423	02/07/1990	EP				N	Y
<i>Lee</i>	B55	1 014 431	06/28/2000	EP				N	N

OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
<i>Lee</i>	C136	International Search Report for International Patent Application No. PCT/US03/26467, dated July 13, 2004, 3 pages.
<i>Lee</i>	C137	Luo <i>et al.</i> , "Compliant effect of low-temperature Si buffer for SiGe growth," <i>Applied Physics Letters</i> , 78(4):454-456 (2001).
<i>Lee</i>	C138	Vyatkin <i>et al.</i> , "Study of Strain Relaxation in Epitaxial Structure GE _{0.2} Si _{0.8} /Si At Thermo-Implantation Treatment by Ion Beam Channeling," <i>Mat. Res. Soc. Symp. Proc.</i> , 585:183-189 (2000).

EXAMINER	<i>Karen May Lee</i>	DATE CONSIDERED
3121278-1		<i>7/26/05</i>